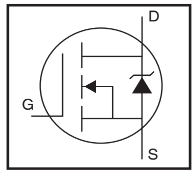
International
IOR Rectifier

AUTOMOTIVE GRADE

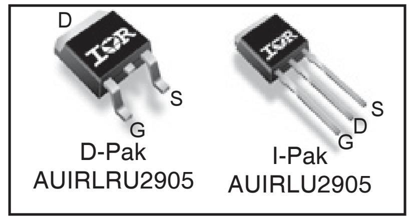
AUIRLR2905
AUIRLU2905

HEXFET® Power MOSFET

- Advanced Planar Technology
- Logic-Level Gate Drive
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified



$V_{(BR)DSS}$	55V
$R_{DS(on)}$ max.	27mΩ
I_D	42A



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLR2905	Dpak	Tube	75	AUIRLR2905
		Tape and Reel	2000	AUIRLR2905TR
		Tape and Reel Left	3000	AUIRLR2905TRL
		Tape and Reel Right	3000	AUIRLR2905TRR
AUIRLU2905	Ipak	Tube	75	AUIRLU2905

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	42	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	30	
I_{DM}	Pulsed Drain Current ①	160	
P_D @T_C = 25°C	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	210	mJ
E_{AS} (tested)	Single Pulse Avalanche Energy Tested Value ⑥	200	
I_{AR}	Avalanche Current ①	25	A
E_{AR}	Repetitive Avalanche Energy ①	11	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

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*Qualification standards can be found at http://www.irf.com/

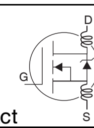
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	——	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ⑤	——	50	
$R_{\theta JA}$	Junction-to-Ambient	——	110	

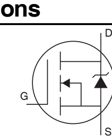
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.070	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.027	Ω	V_{GS} = 10V, I_D = 25A ④
		——	——	0.030		V_{GS} = 5.0V, I_D = 25A ④
		——	——	0.040		V_{GS} = 4.0V, I_D = 21A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
gfs	Forward Transconductance	21	——	——	S	V_{DS} = 25V, I_D = 25A
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	µA	V_{DS} = 55V, V_{GS} = 0V
		——	——	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	——	——	48	nC	I_D = 25A
Q_{gs}	Gate-to-Source Charge	——	——	8.6		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	25		V_{GS} = 5.0V ④
$t_{d(on)}$	Turn-On Delay Time	——	11	——	ns	V_{DD} = 28V
t_r	Rise Time	——	84	——		I_D = 25A
$t_{d(off)}$	Turn-Off Delay Time	——	26	——		R_G = 3.4Ω
t_f	Fall Time	——	15	——		V_{GS} = 5.0V, R_D = 1.1Ω ④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	——	7.5	——		
C_{iss}	Input Capacitance	——	1700	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	400	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	150	——		f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	42	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	160		
V_{SD}	Diode Forward Voltage	——	——	1.3	V	T_J = 25°C, I_S = 25A, V_{GS} = 0V ④
dv/dt	Peak Diode Recovery ③	——	5.0	——	V/ns	T_J = 175°C, I_S = 25A, V_{DS} = 55V
t_{rr}	Reverse Recovery Time	——	80	120	ns	T_J = 25°C, I_F = 25A
Q_{rr}	Reverse Recovery Charge	——	210	320	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L = 470µH R_G = 25Ω, I_{AS} = 25A. (See Figure 12)

③ $I_{SD} \leq$ 25A, di/dt $\leq$ 270A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width $\leq$ 300µs; duty cycle $\leq$ 2%.

⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

⑥ R_θ is measured at Tj approximately 90°C.

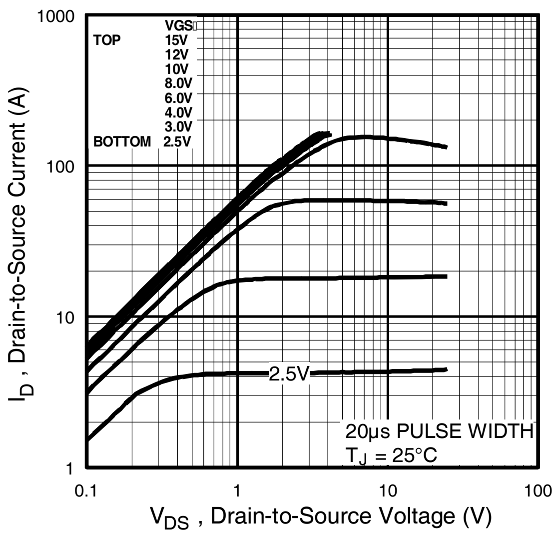


Fig 1. Typical Output Characteristics

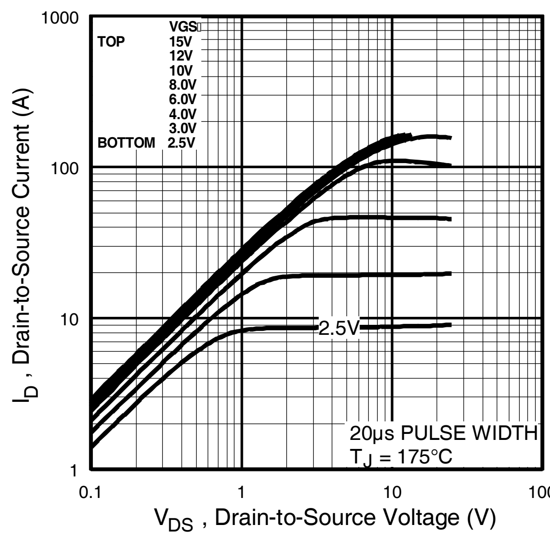


Fig 2. Typical Output Characteristics

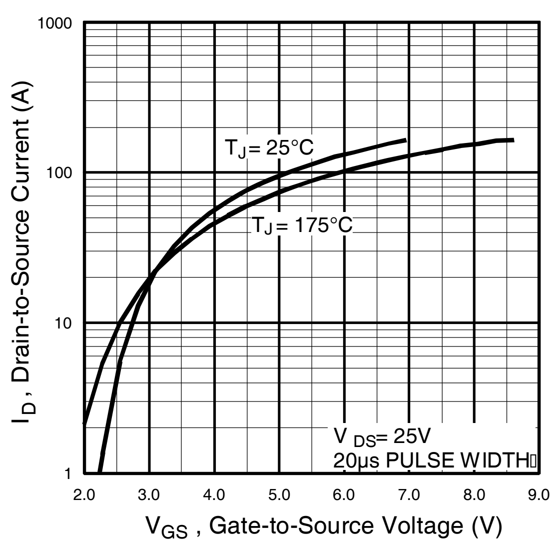


Fig 3. Typical Transfer Characteristics

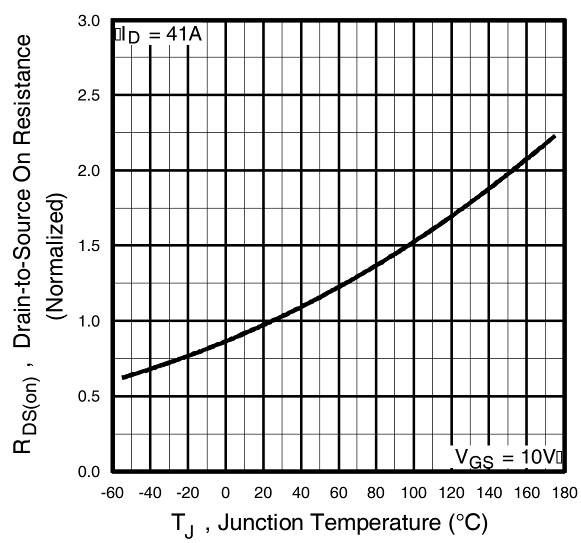


Fig 4. Normalized On-Resistance Vs. Temperature

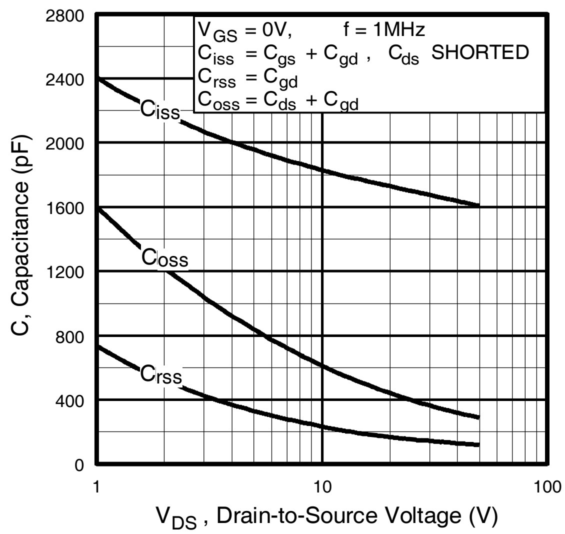


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

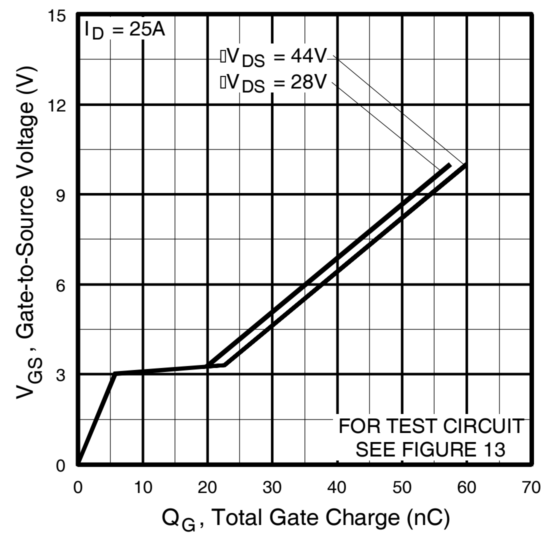


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

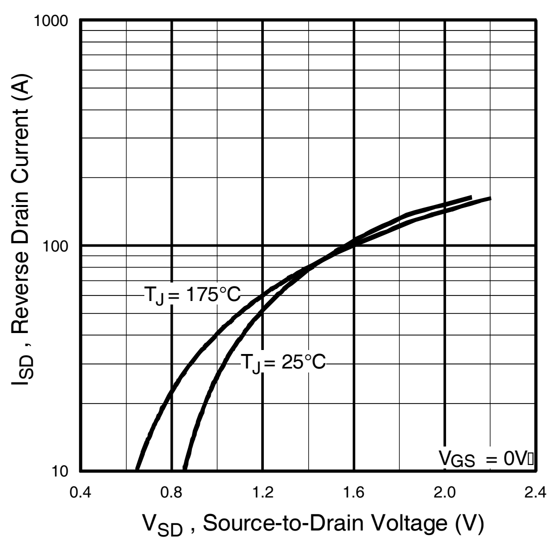


Fig 7. Typical Source-Drain Diode Forward Voltage

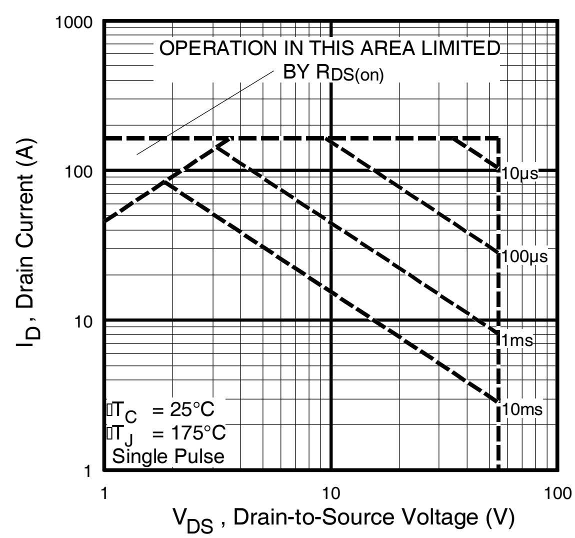


Fig 8. Maximum Safe Operating Area

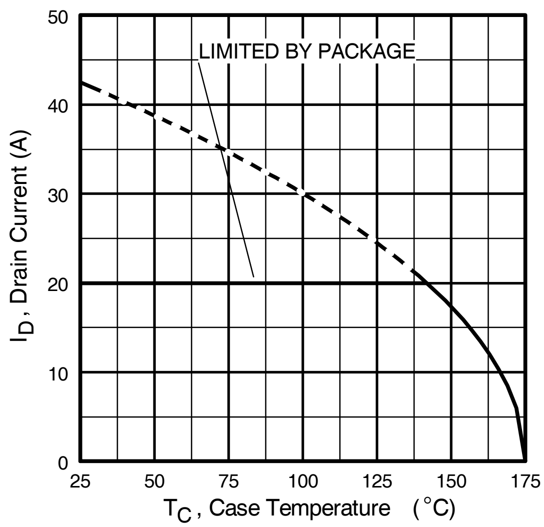


Fig 9. Maximum Drain Current Vs. Case Temperature

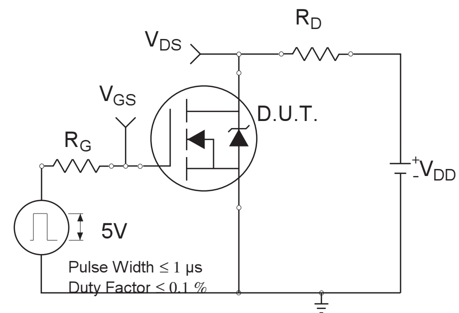


Fig 10a. Switching Time Test Circuit

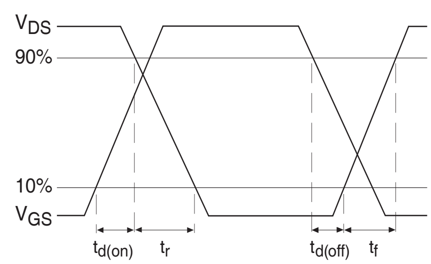


Fig 10b. Switching Time Waveforms

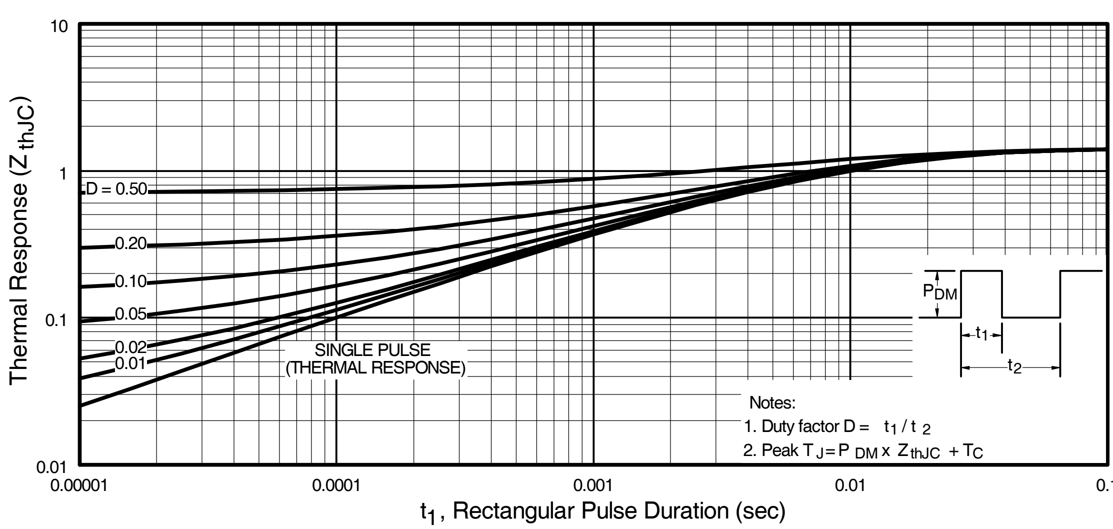


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

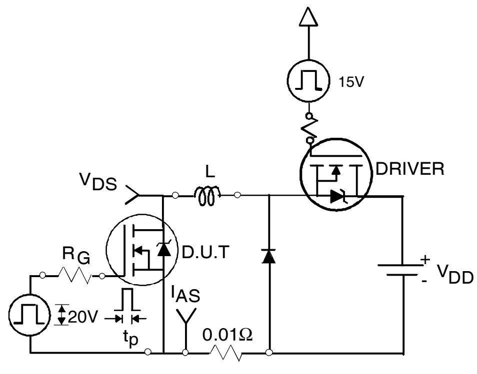


Fig 12a. Unclamped Inductive Test Circuit

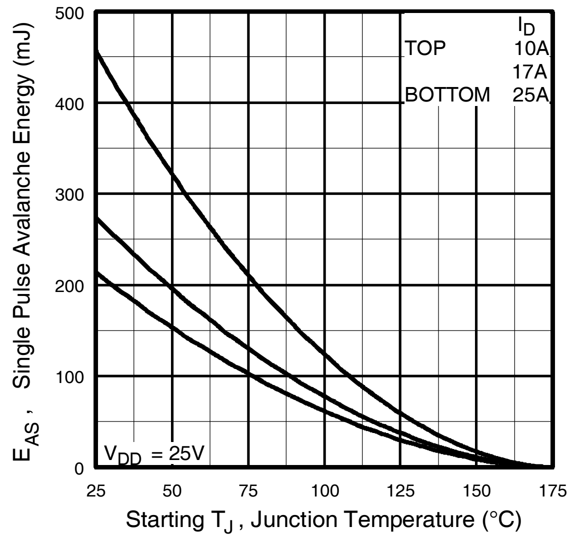


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

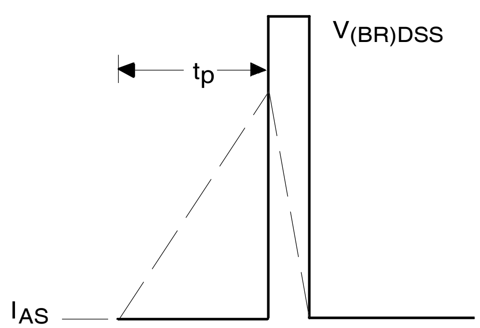


Fig 12b. Unclamped Inductive Waveforms

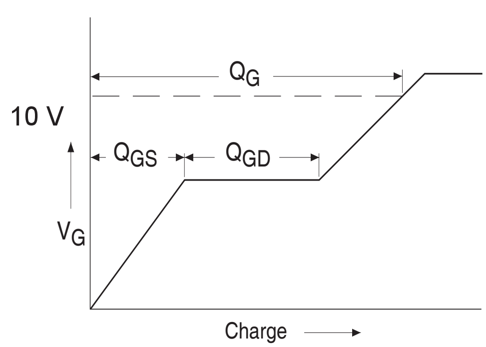


Fig 13a. Basic Gate Charge Waveform

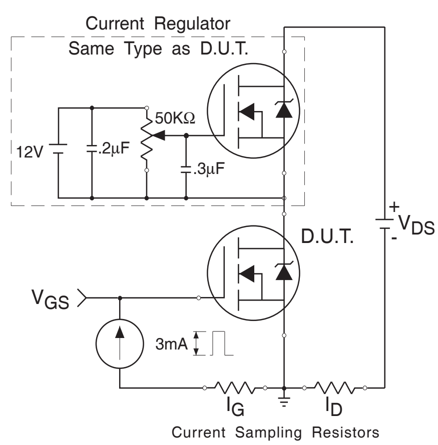
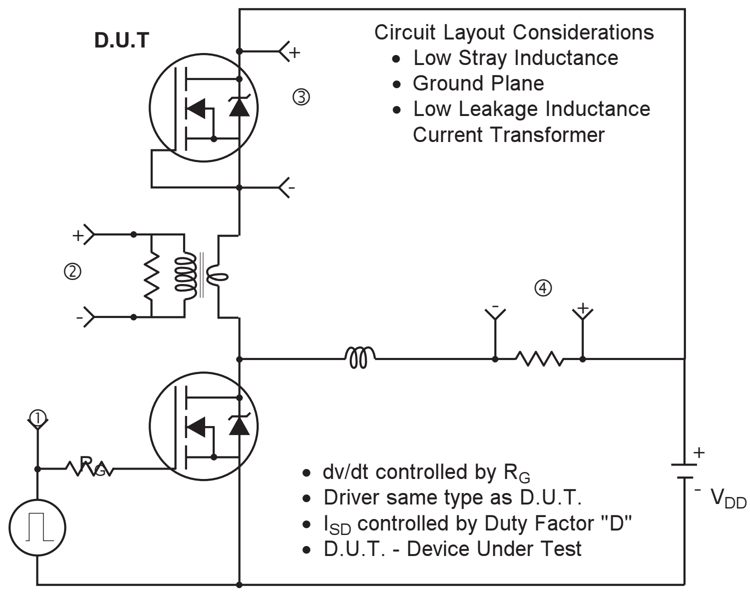
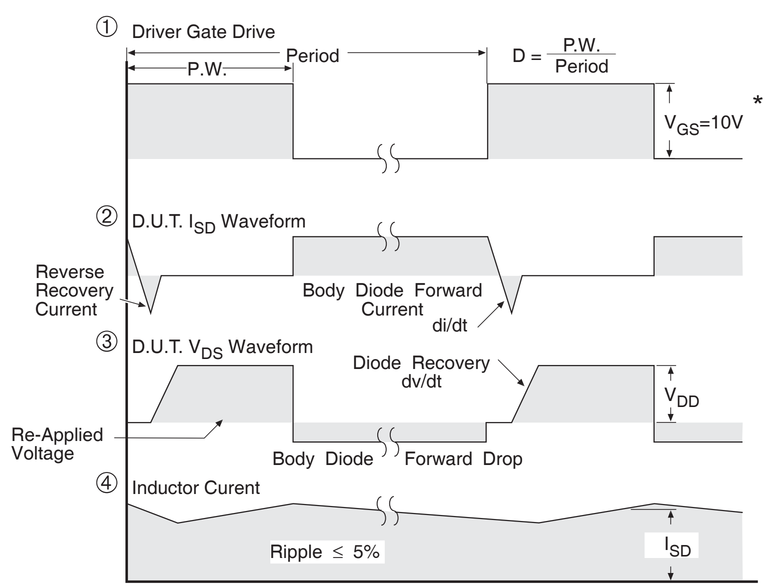


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



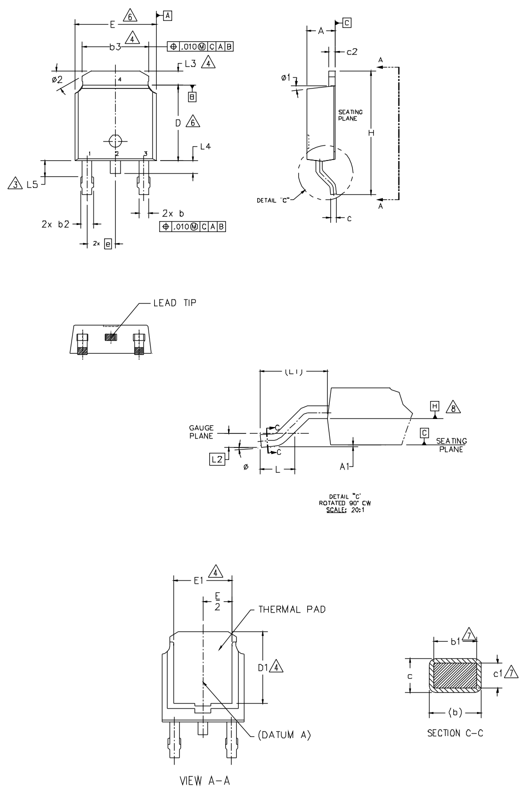


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
3.- LEAD DIMENSION UNCONTROLLED IN L5.
4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	–	0.13	–	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	–	.205	–	4
E	6.35	6.73	.250	.265	6
E1	4.32	–	.170	–	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	–	1.02	–	.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

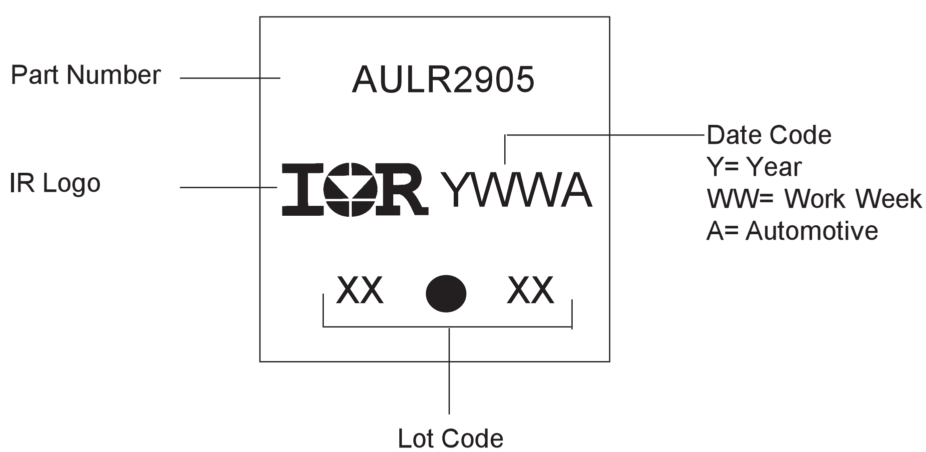
HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

IGBT & CoPAK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

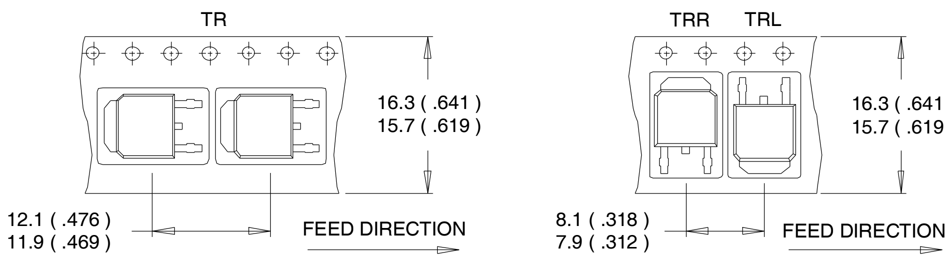
D-Pak Part Marking Information



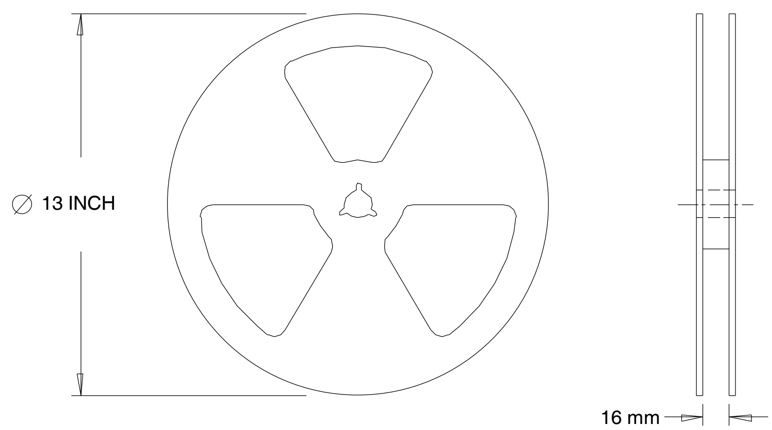
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

<table>
<tr><td colspan="2" rowspan="2">Qualification Level</td><td colspan="2">Automotive
(per AEC-Q101)</td></tr>
<tr><td colspan="2">Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.</td></tr>
<tr><td colspan="2" rowspan="2">Moisture Sensitivity Level</td><td>D-PAK</td><td>MSL1</td></tr>
<tr><td>I-PAK</td><td>MSL1</td></tr>
<tr><td rowspan="3">ESD</td><td>Machine Model</td><td colspan="2">Class M4 (+/- 425V)††
AEC-Q101-002</td></tr>
<tr><td>Human Body Model</td><td colspan="2">Class H1B (+/- 1000V)††
AEC-Q101-001</td></tr>
<tr><td>Charged Device Model</td><td colspan="2">Class C5 (+/- 1125V)††
AEC-Q101-005</td></tr>
<tr><td colspan="2">RoHS Compliant</td><td colspan="2">Yes</td></tr>
</table>

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Highest passing voltage.

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http://www.irf.com/technical-info/

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Tel: (310) 252-7105

